

SN74CB3T3125 クワッドFETバス・スイッチ

2.5V、3.3V低電圧バス・スイッチ、5V耐圧レベル・シフト付き

1 特長

- 出力電圧変換が V_{CC} に追従
- すべてのデータI/Oポートで混在モード信号動作をサポート
 - 3.3Vの V_{CC} の場合、5V入力を3.3V出力にレベル・シフト
 - 2.5Vの V_{CC} の場合、5V/3.3V入力を2.5V出力にレベル・シフト
- デバイスの電源オン時とオフ時の両方で5V許容のI/O
- 伝播遅延がゼロに近い双方向データ・フロー
- 低いオン抵抗(r_{on})特性 ($r_{on} = 5\Omega$: 標準値)
- 低い入力/出力容量により負荷が最小化
($C_{io(OFF)} = 4.5pF$: 標準値)
- データおよび制御入力にアンダーシュート・クランプ・ダイオードを搭載
- 低い消費電力 ($I_{CC} = 20\mu A$: 最大値)
- 2.3V~3.6Vの範囲の V_{CC} で動作
- データI/Oは0~5Vの信号レベルに対応(0.8V、1.2V、1.5V、1.8V、2.5V、3.3V、5V)
- 制御入力をTTLまたは5V/3.3V CMOS出力で駆動可能
- I_{off} により部分的パワーダウン・モード動作をサポート
- JESD 17準拠で250mA超のラッチアップ性能
- JESD 22準拠でESD性能をテスト済み
 - 人体モデルで2000V (A114-B、クラスII)
 - 荷電デバイス・モデルで1000V (C101)

2 アプリケーション

- デジタル・アプリケーションをサポート: レベル変換、USBインターフェイス、バス分離
- 低消費電力の携帯用機器に理想的

3 概要

SN74CB3T3125は、オン抵抗(r_{on})が低い伝播遅延を最小限に低減できる高速TTL互換FETバス・スイッチです。このデバイスは、 V_{CC} に追従した電圧変換を行うことで、すべてのデータI/Oポートにおいて混在モード信号動作を完全にサポートします。SN74CB3T3125は、5V TTL、3.3V LVTTTL、2.5V CMOSスイッチング規格に加えて、ユーザー定義のスイッチング・レベルを使用するシステムに対応します(「標準的なDC電圧変換特性」を参照)。

SN74CB3T3125は4つの1ビット・バス・スイッチとして構成され、個別の出力イネーブル($1\overline{OE}$ 、 $2\overline{OE}$ 、 $3\overline{OE}$ 、 $4\overline{OE}$)入力を持っています。このデバイスは、4つの1ビット・バス・スイッチ、または1つの4ビット・バス・スイッチとして使用できます。 $\overline{OE}$ がLOWのとき、関連付けられている1ビット・バス・スイッチはオンで、AポートはBポートに接続され、ポート間で双方向のデータ・フローが可能になります。 $\overline{OE}$ をHIGHにすると、関連する1ビット・バス・スイッチはオフになり、AとBのポート間には高インピーダンス状態になります。

このデバイスは、 I_{off} を使用する部分的パワーダウン・アプリケーション用に完全に動作が規定されています。 I_{off} 機能により、パワーダウン時に損傷を引き起こすような電流がデバイスに逆流しないことが保証されます。デバイスは、電源オフ時は絶縁されています。

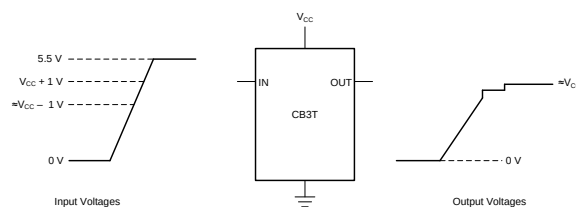
電源オンまたは電源オフ時に高インピーダンス状態を確保するため、 $\overline{OE}$ はプルアップ抵抗経路で V_{CC} に接続します。この抵抗の最小値は、ドライバの電流シンク能力によって決定されます。

製品情報⁽¹⁾

型番	パッケージ	本体サイズ(公称)
SN74CB3T3125	VQFN – RGY (14)	3.50mm×3.50mm
	TSSOP – PW (14)	5.00mm×4.40mm
	TVSOP – DGV (14)	3.60mm×4.40mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。

標準的なDC電圧変換特性



If the input high voltage (V_{IH}) level is greater than or equal to $V_{CC} + 1V$, and less than or equal to 5.5 V, the output high voltage (V_{OH}) level will be equal to approximately the V_{CC} voltage level.

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4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Revision B (August 2012) から Revision C に変更

Page

• 「アプリケーション」一覧、「製品情報」表、「ESD定格」表、「機能説明」セクション、「デバイスの機能モード」セクション、「アプリケーションと実装」セクション、「電源に関する推奨事項」セクション、「レイアウト」セクション、「デバイスおよびドキュメントのサポート」セクション、「メカニカル、パッケージ、および注文情報」セクションを追加	1
• 「注文情報」表を削除	1
• Changed t_{en} $V_{CC} = 3.3$ V MAX value From: 4.4 ns To: 8 ns in the <i>Switching Characteristic</i>	5

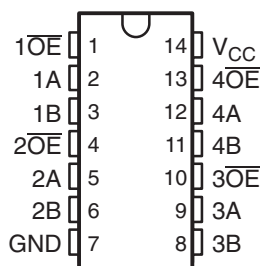
Revision A (April 2009) から Revision B に変更

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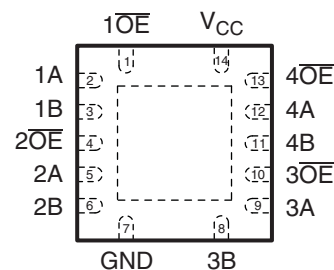
• 「標準的なDC電圧変換特性」を更新	1
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5 Pin Configuration and Functions

**DGV OR PW PACKAGE
(TOP VIEW)**



**RGY PACKAGE
(TOP VIEW)**



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
$\overline{1OE}$	1	I	Active-low enable for switch 1
1A	2	I/O	Switch 1 A terminal
1B	3	I/O	Switch 1 B terminal
$\overline{2OE}$	4	I	Active-low enable for switch 2
2A	5	I/O	Switch 2 A terminal
2B	6	I/O	Switch 2 B terminal
GND	7	-	Ground
3A	8	I/O	Switch 3 A terminal
3B	9	I/O	Switch 3 B terminal
$\overline{3OE}$	10	I	Active-low enable for switch 3
4A	11	I/O	Switch 4 A terminal
4B	12	I/O	Switch 4 B terminal
$\overline{4OE}$	13	I	Active-low enable for switch 4
V_{CC}	14	-	Supply voltage pin

6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V _{CC}	Supply voltage range ⁽²⁾	–0.5	7	V
V _{IN}	Control input voltage range ^{(2) (3)}	–0.5	7	V
V _{I/O}	Switch I/O voltage range ^{(2) (3) (4)}	–0.5	7	V
I _{IK}	Control input clamp current	V _{IN} < 0		–50 mA
I _{I/OK}	I/O port clamp current	V _{I/O} < 0		–50 mA
I _{I/O}	ON-state switch current ⁽⁵⁾		±128	mA
	Continuous current through V _{CC} or GND		±100	mA
T _{stg}	Storage temperature range	–65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to ground unless otherwise specified.
- (3) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (4) V_I and V_O are used to denote specific conditions for V_{I/O}.
- (5) I_I and I_O are used to denote specific conditions for I_{I/O}.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	2.3	3.6	V
V _{IH}	High-level control input voltage	V _{CC} = 2.3 V to 2.7 V	1.7	5.5
		V _{CC} = 2.7 V to 3.6 V	2	5.5
V _{IL}	Low-level control input voltage	V _{CC} = 2.3 V to 2.7 V	0	0.7
		V _{CC} = 2.7 V to 3.6 V	0	0.8
V _{I/O}	Data input/output voltage	0	5.5	V
T _A	Operating free-air temperature	–40	85	°C

- (1) All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number [SCBA004](#).

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74CB3T3125			UNIT
		VQFN (RGY)	TSSOP (PW)	TVSOP (DGV)	
		14 PINS	14 PINS	14 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	55.5	123.3	154.8	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	56.9	53.0	64.4	°C/W
R _{θJB}	Junction-to-board thermal resistance	30.9	66.3	88.4	°C/W
ψ _{JT}	Junction-to-top characterization parameter	3.6	9.1	10.8	°C/W
ψ _{JB}	Junction-to-board characterization parameter	30.9	65.7	87.4	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	14.6	-	-	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics⁽¹⁾

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
V_{IK}		$V_{CC} = 3\text{ V}$, $I_I = -18\text{ mA}$			-1.2	V
V_{OH}		See Figure 3 through Figure 5				
I_{IN}	Control inputs	$V_{CC} = 3.6\text{ V}$, $V_{IN} = 3.6\text{ V}$ to 5.5 V or GND			±10	μA
I_I		$V_{CC} = 3.6\text{ V}$, Switch ON, $V_{IN} = V_{CC}$ or GND	$V_I = V_{CC} - 0.7\text{ V}$ to 5.5 V		±20	μA
			$V_I = 0.7\text{ V}$ to $V_{CC} - 0.7\text{ V}$		-40	
			$V_I = 0$ to 0.7 V		±5	
I_{OZ} ⁽³⁾		$V_{CC} = 3.6\text{ V}$, $V_O = 0$ to 5.5 V , $V_I = 0$, Switch OFF, $V_{IN} = V_{CC}$ or GND			±10	μA
I_{off}		$V_{CC} = 0$, $V_O = 0$ to 5.5 V , $V_I = 0$			10	μA
I_{CC}		$V_{CC} = 3.6\text{ V}$, $I_{I/O} = 0$, Switch ON or OFF, $V_{IN} = V_{CC}$ or GND	$V_I = V_{CC}$ or GND		20	μA
			$V_I = 5.5\text{ V}$		20	
ΔI_{CC} ⁽⁴⁾	Control inputs	$V_{CC} = 3\text{ V}$ to 3.6 V , One input at $V_{CC} - 0.6\text{ V}$, Other inputs at V_{CC} or GND			300	μA
C_{in}	Control inputs	$V_{CC} = 3.3\text{ V}$, $V_{IN} = V_{CC}$ or GND		3		pF
$C_{io(OFF)}$		$V_{CC} = 3.3\text{ V}$, $V_{I/O} = 5.5\text{ V}$, 3.3 V , or GND, Switch OFF, $V_{IN} = V_{CC}$ or GND		4.5		pF
$C_{io(ON)}$		$V_{CC} = 3.3\text{ V}$, Switch ON, $V_{IN} = V_{CC}$ or GND	$V_{I/O} = 5.5\text{ V}$ or 3.3 V		4	pF
			$V_{I/O} = \text{GND}$		10	
r_{on} ⁽⁵⁾		$V_{CC} = 2.3\text{ V}$, TYP at $V_{CC} = 2.5\text{ V}$, $V_I = 0$	$I_O = 24\text{ mA}$		5	Ω
			$I_O = 16\text{ mA}$		5	
		$V_{CC} = 3\text{ V}$, $V_I = 0$	$I_O = 64\text{ mA}$		5	
			$I_O = 32\text{ mA}$		5	

(1) V_{IN} and I_{IN} refer to control inputs. V_I , V_O , I_I , and I_O refer to data pins.

(2) All typical values are at $V_{CC} = 3.3\text{ V}$ (unless otherwise noted), $T_A = 25^\circ\text{C}$.

(3) For I/O ports, the parameter I_{OZ} includes the input leakage current.

(4) This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V_{CC} or GND.

(5) Measured by the voltage drop between A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 6)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 2.5\text{ V}$ $\pm 0.2\text{ V}$		$V_{CC} = 3.3\text{ V}$ $\pm 0.3\text{ V}$		UNIT
			MIN	MAX	MIN	MAX	
t_{pd} ⁽¹⁾	A or B	B or A	0.15		0.25		ns
t_{en}	$\overline{OE}$	A or B	1	8.5	1	8	ns
t_{dis}	$\overline{OE}$	A or B	1	9	1	9	ns

(1) The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

6.7 Typical Characteristics

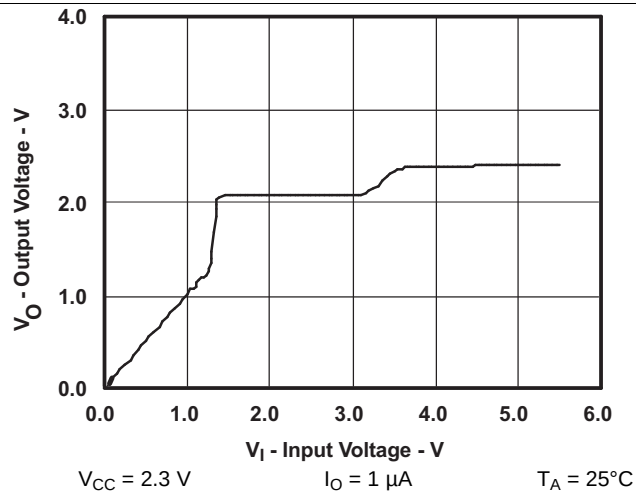


Figure 1. Data Output Voltage vs Data Input Voltage

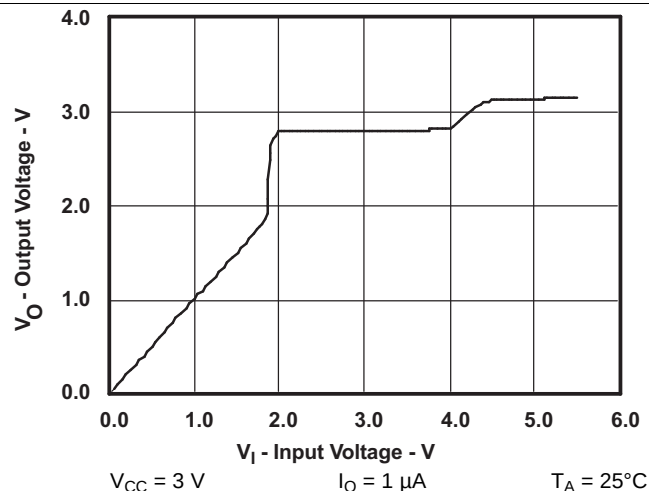


Figure 2. Data Output Voltage vs Data Input Voltage

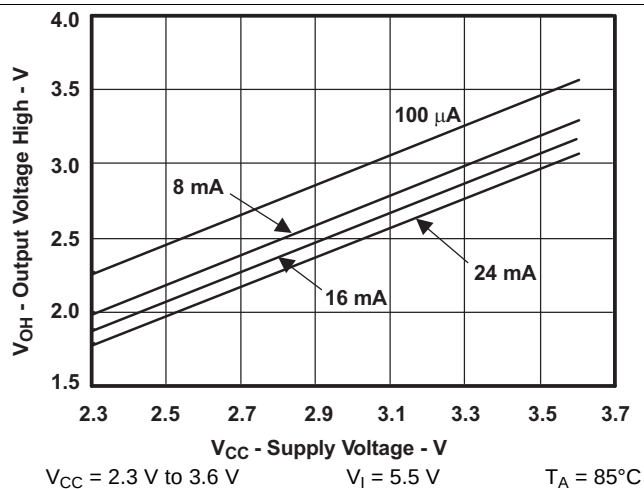


Figure 3. Output Voltage High vs Supply Voltage

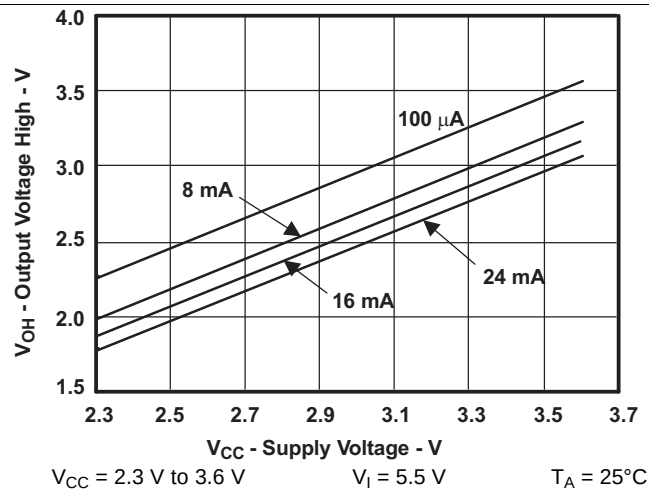


Figure 4. Output Voltage High vs Supply Voltage

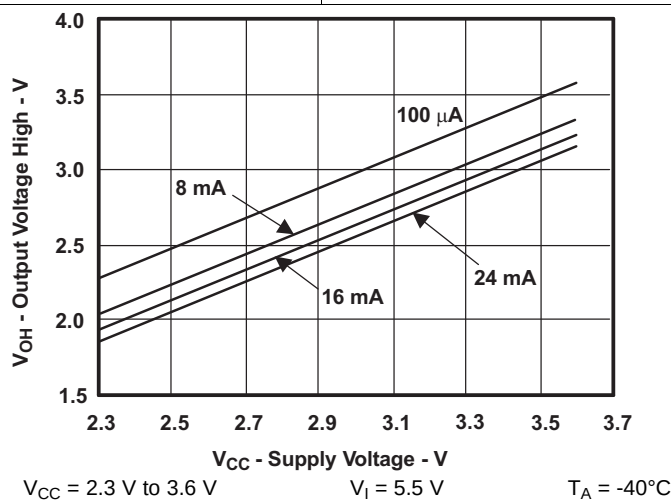
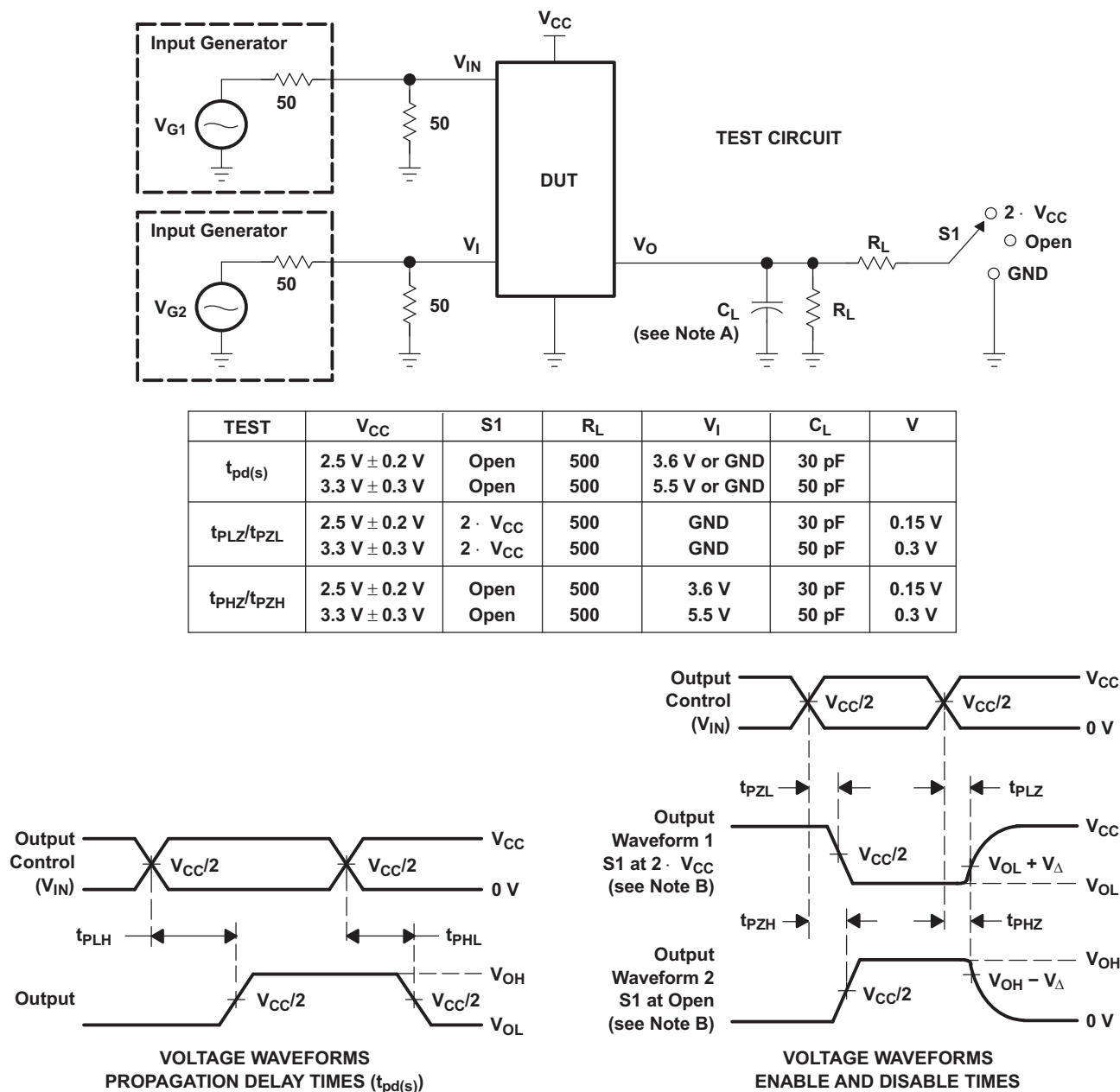


Figure 5. Output Voltage High vs Supply Voltage

7 Parameter Measurement Information



- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: PRR = 10 MHz, Z_O = 50 Ω, t_r = 2.5 ns, t_f = 2.5 ns.
 - The outputs are measured one at a time, with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis}.
 - t_{PZL} and t_{PZH} are the same as t_{en}.
 - t_{PLH} and t_{PHL} are the same as t_{pd(s)}. The t_{pd} propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
 - All parameters and waveforms are not applicable to all devices.

Figure 6. Test Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

The SN74CB3T3215 device is organized as four 1-bit bus switches with separate output-enable (1OE, 2OE, 3OE, and 4 OE) inputs. When OE is low, the associated 1-bit bus switch is ON, and the A port is connected to the B port, allowing bidirectional data flow between ports. When OE is high, the associated 1-bit bus switch is OFF, and a high-impedance state exists between the A and B ports. This device is fully specified for partial-power-down applications using I_{off}. The I_{off} feature ensures that damaging current will not backflow through the device when it is powered down. The SN74CB3T3215 device has isolation during power off. To ensure the high-impedance state during power up or power down, OE should be tied to VCC through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

8.2 Functional Block Diagram

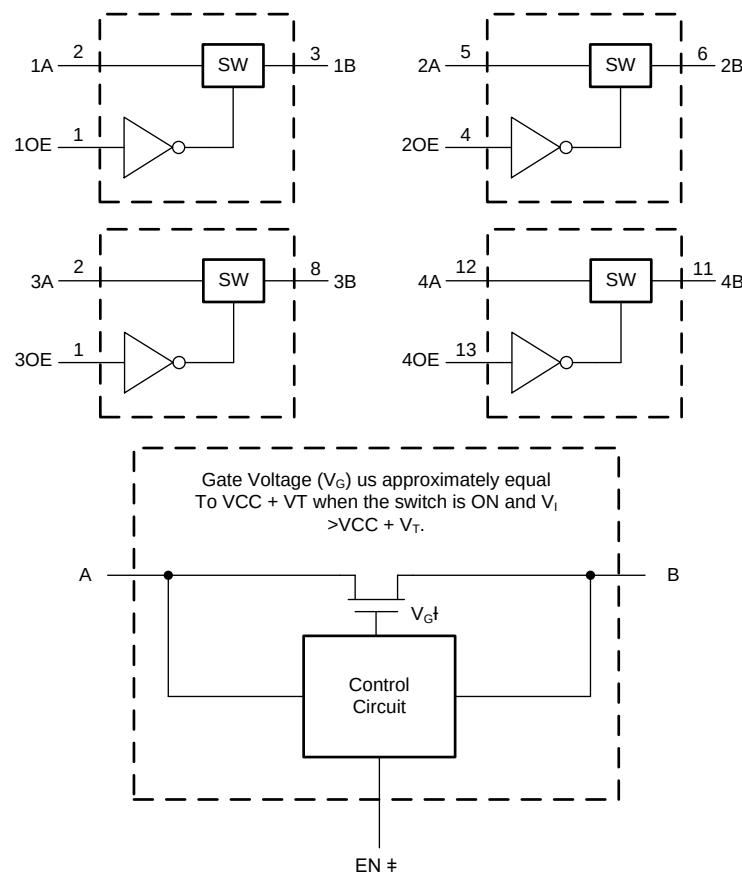


Figure 7. Simplified Schematic, Each FET Switch (SW)

8.3 Feature Description

The SN74CB3T3125 is ideal for low-power portable equipment. Power consumption is low by design, $I_{CC} = 20 \mu A$, On-state resistance is low ($r_{on} = 5 \Omega$) It has bidirectional data flow with near zero propagation delay. The device minimizes loading due to the low input/output capacitance $C_{io(OFF)} = 4.5 pF$ Typical. Operating VCC range from 2.3 V to 3.6 V. The output tracks VCC. Data and control inputs provide undershoot clamp diodes. Control inputs can be driven by TTL or 5-V/3.3-V CMOS outputs. It supports mixed-mode signal operation on all data I/O ports. Data I/Os support 0- to 5-V signaling levels (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.3 V, 5 V). The device is protected from damaging current, loff supports partial shutdown which prevents the current from flowing back through the device when it is powered down. In addition, it has 5-V tolerant I/Os with device powered up or powered down. The device is latch-up resistant with 250 mA exceeding the JESD 17 standard, providing protection from destruction due to latch-up. This device is protected against electrostatic discharge. It is tested per JESD 22 using 2000-V Human-Body Model (A114-B, Class II), and 1000-V Charged-Device Model (C101).

8.4 Device Functional Modes

Table 1 lists the functional modes for the SN74CB3T3125.

**Table 1. Function Table
(Each Bus Switch)**

INPUT OE	INPUT/OUTPUT A	FUNCTION
L	B	A port = B port
H	Z	Disconnect

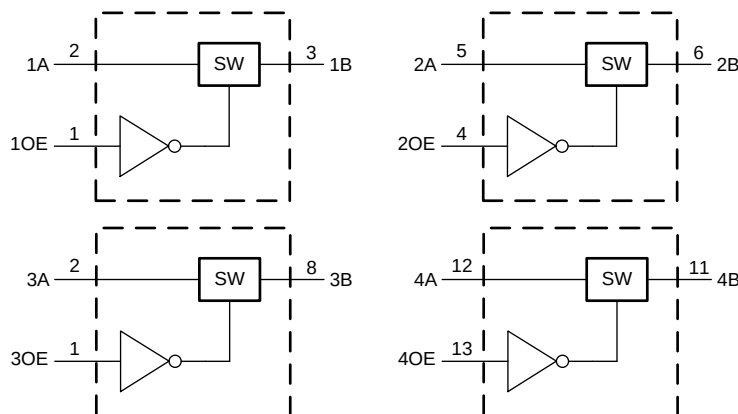


Figure 8. Logic Diagram (Positive Logic)

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

This application is specifically to connect a 5-V bus to a 3.3 V device. Ideally, set VCC to 3.3 V. It is assumed that communication in this particular application is one-directional, going from the bus controller to the device.

9.2 Typical Application

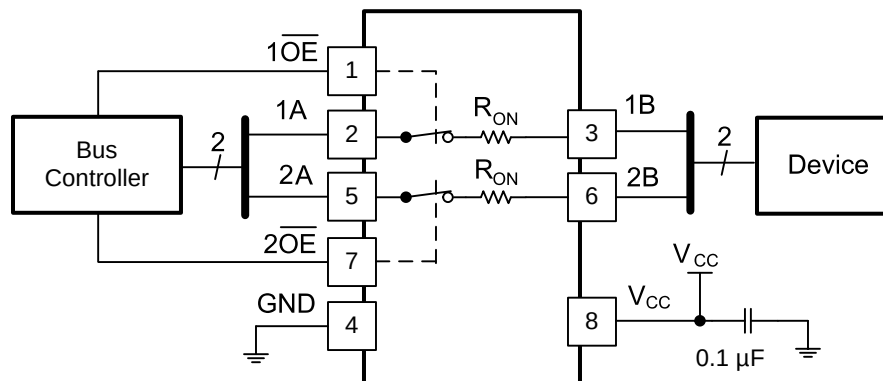


Figure 9. Application Circuit

9.2.1 Design Requirements

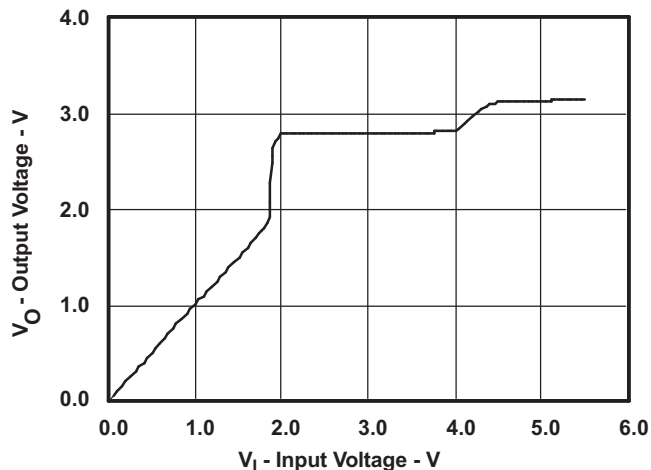
This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. Because this design is for down-translating voltage, no pull-up resistors are required.

9.2.2 Detailed Design Procedure

1. Recommended Input conditions – Specified high and low levels. See (V_{IH} and V_{IL}) in *Recommended Operating Conditions* – Inputs are overvoltage tolerant allowing them to go as high as 7 V at any valid VCC.
2. Recommend output conditions – Load currents should not exceed 128 mA on each channel.

Typical Application (continued)

9.2.3 Application Curves



$$V_{CC} = 3\text{ V}$$

$$I_O = 1\text{ }\mu\text{A}$$

$$T_A = 25^\circ\text{C}$$

Figure 10. Data Output Voltage vs Data Input Voltage

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the Recommended Operating Conditions.

Each VCC terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μF bypass capacitor is recommended. If there are multiple pins labeled VCC, then a 0.01- μF or 0.022- μF capacitor is recommended for each VCC because the VCC pins will be tied together internally. For devices with dual supply pins operating at different voltages, for example VCC and VDD, a 0.1- μF bypass capacitor is recommended for each supply pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1- μF and 1- μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

11 Layout

11.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self-inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. Figure 11 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

11.2 Layout Example

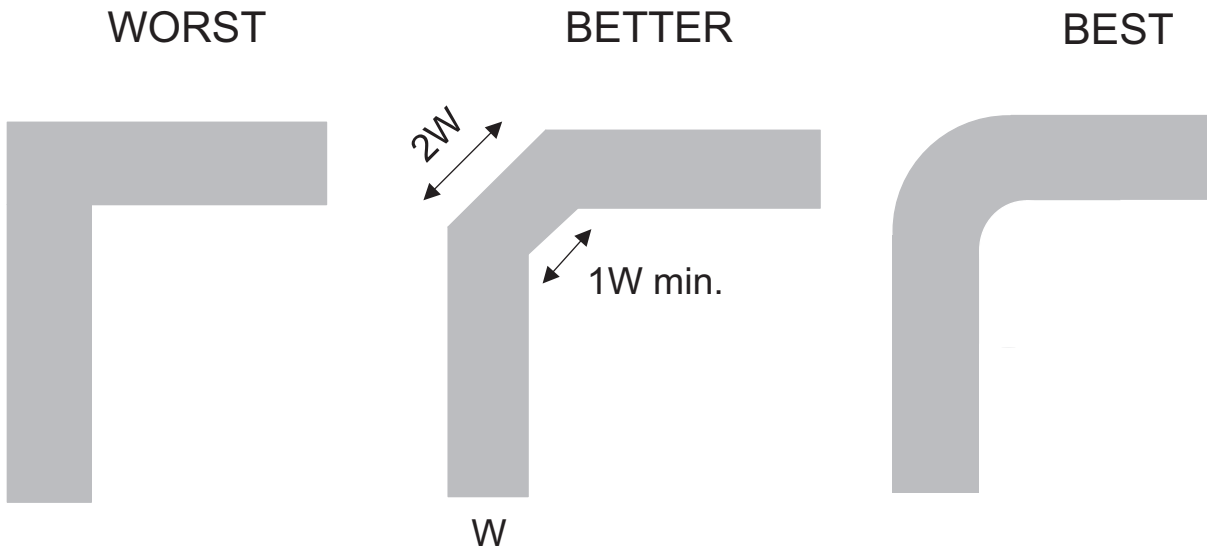


Figure 11. Example Layout

12 デバイスおよびドキュメントのサポート

12.1 デバイス・サポート

12.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.comのデバイス製品フォルダを開いてください。右上の「アラートを受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

12.3 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ オンライン・コミュニティ TIのE2E (*Engineer-to-Engineer*) コミュニティ。エンジニア間の共同作業を促進するために開設されたものです。e2e.ti.comでは、他のエンジニアに質問し、知識を共有し、アイデアを検討して、問題解決に役立てることができます。

設計サポート TIの設計サポート 役に立つE2Eフォーラムや、設計サポート・ツールをすばやく見つけることができます。技術サポート用の連絡先情報も参照できます。

12.4 商標

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12.5 静電気放電に関する注意事項



すべての集積回路は、適切なESD保護方法を用いて、取扱いと保存を行うようにして下さい。

静電気放電はわずかな性能の低下から完全なデバイスの故障に至るまで、様々な損傷を与えます。高精度の集積回路は、損傷に対して敏感であり、極めてわずかなパラメータの変化により、デバイスに規定された仕様に適合しなくなる場合があります。

12.6 Glossary

[SLYZ022](#) — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74CB3T3125DGVR	Active	Production	TVSOP (DGV) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS125
SN74CB3T3125DGVR.B	Active	Production	TVSOP (DGV) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS125
SN74CB3T3125DGVRG4	Active	Production	TVSOP (DGV) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS125
SN74CB3T3125DGVRG4.B	Active	Production	TVSOP (DGV) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS125
SN74CB3T3125PW	Obsolete	Production	TSSOP (PW) 14	-	-	Call TI	Call TI	-40 to 85	KS125
SN74CB3T3125PWR	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS125
SN74CB3T3125PWR.B	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS125
SN74CB3T3125RGYR	Active	Production	VQFN (RGY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	KS125
SN74CB3T3125RGYR.B	Active	Production	VQFN (RGY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	KS125

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

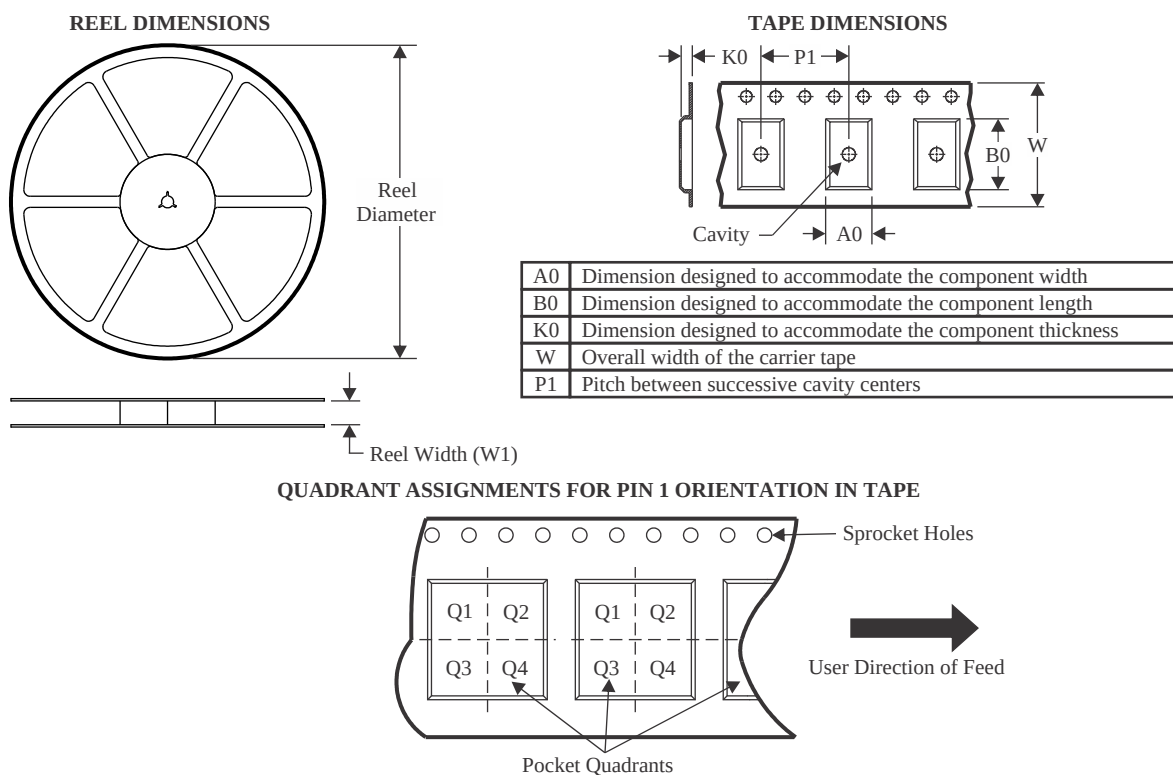
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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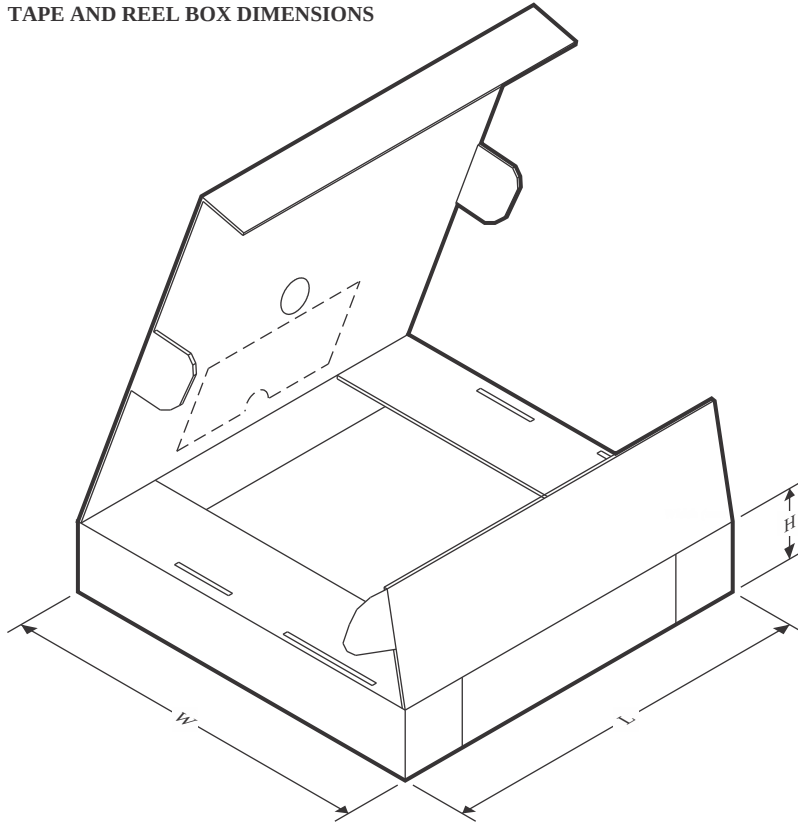
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74CB3T3125DGVR	TVSOP	DGV	14	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CB3T3125DGVRG4	TVSOP	DGV	14	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CB3T3125PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CB3T3125RGYR	VQFN	RGY	14	3000	330.0	12.4	3.75	3.75	1.15	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



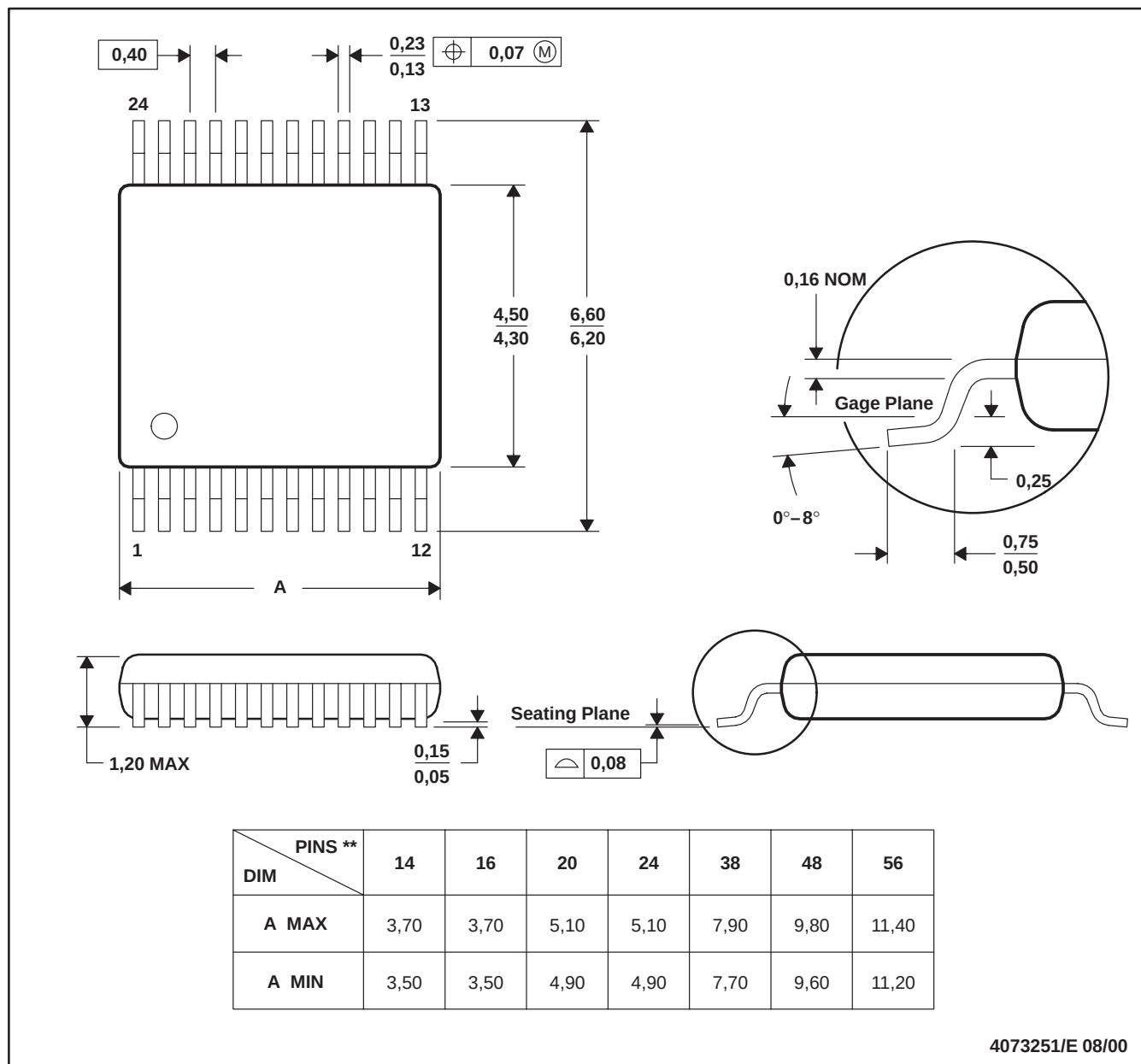
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74CB3T3125DGVR	TVSOP	DGV	14	2000	353.0	353.0	32.0
SN74CB3T3125DGVRG4	TVSOP	DGV	14	2000	353.0	353.0	32.0
SN74CB3T3125PWR	TSSOP	PW	14	2000	353.0	353.0	32.0
SN74CB3T3125RGYR	VQFN	RGY	14	3000	353.0	353.0	32.0

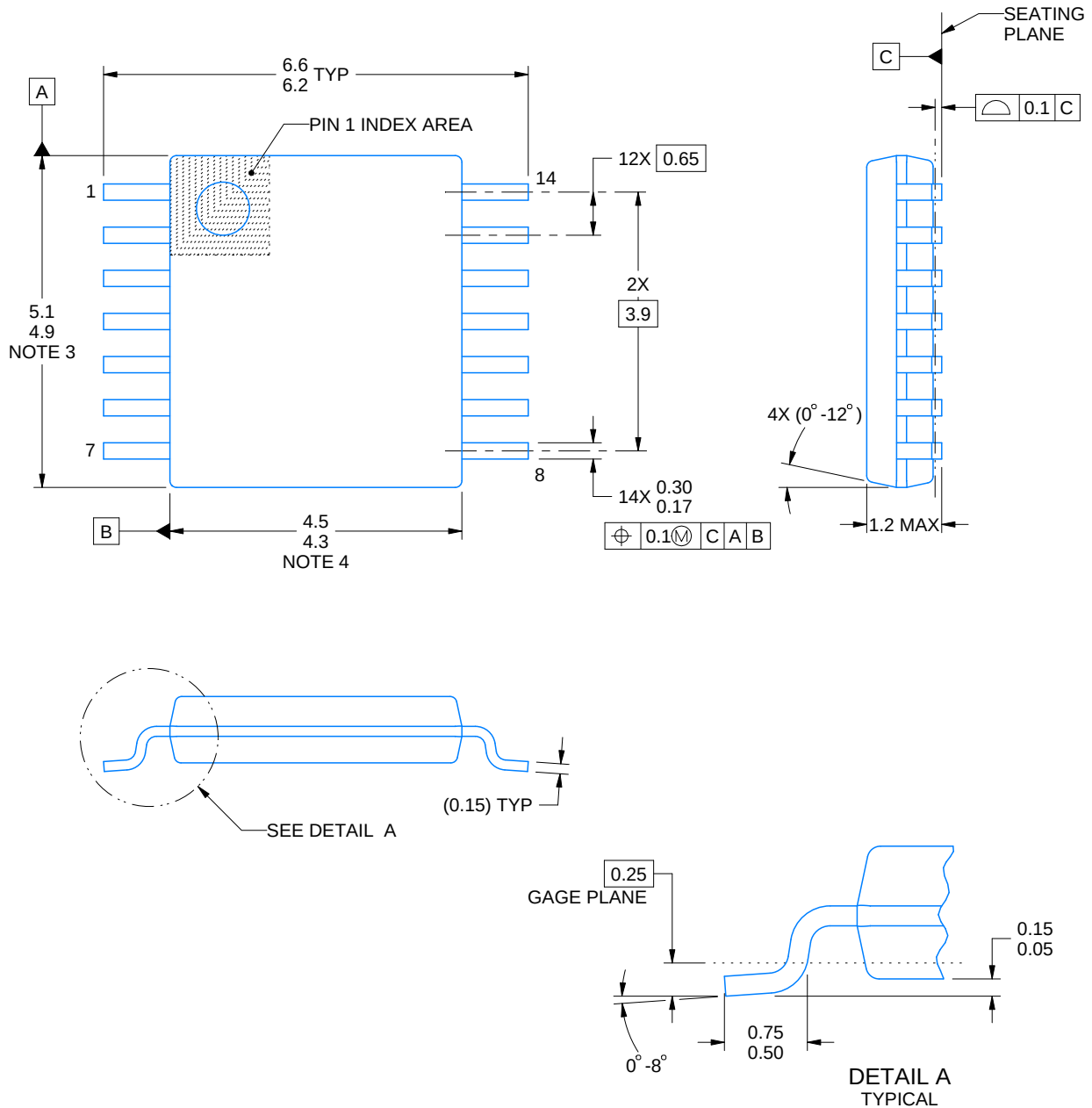
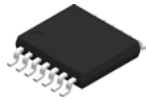
DGV (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

24 PINS SHOWN



- NOTES: A. All linear dimensions are in millimeters.
 B. This drawing is subject to change without notice.
 C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
 D. Falls within JEDEC: 24/48 Pins – MO-153
 14/16/20/56 Pins – MO-194



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NOTES:

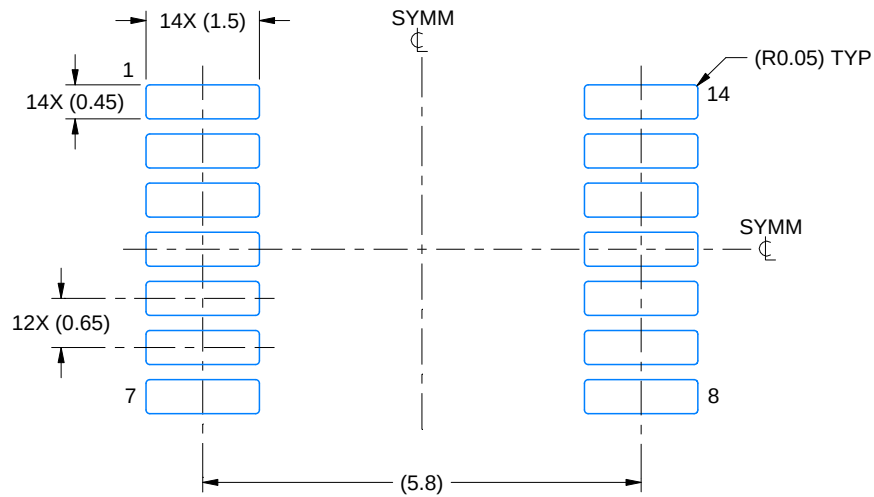
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

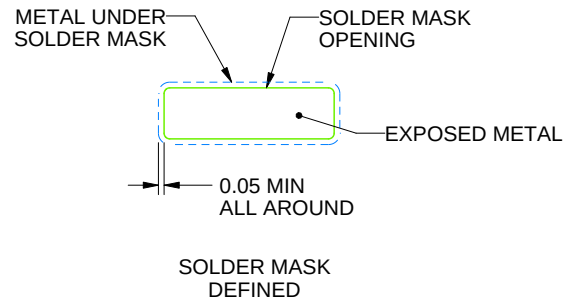
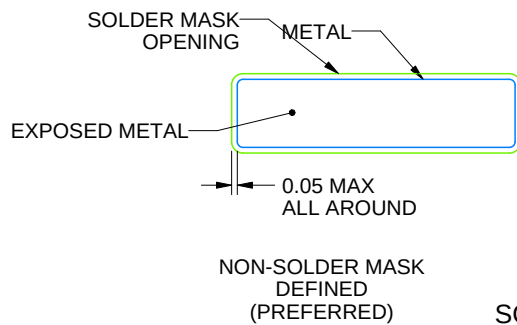
PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

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NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

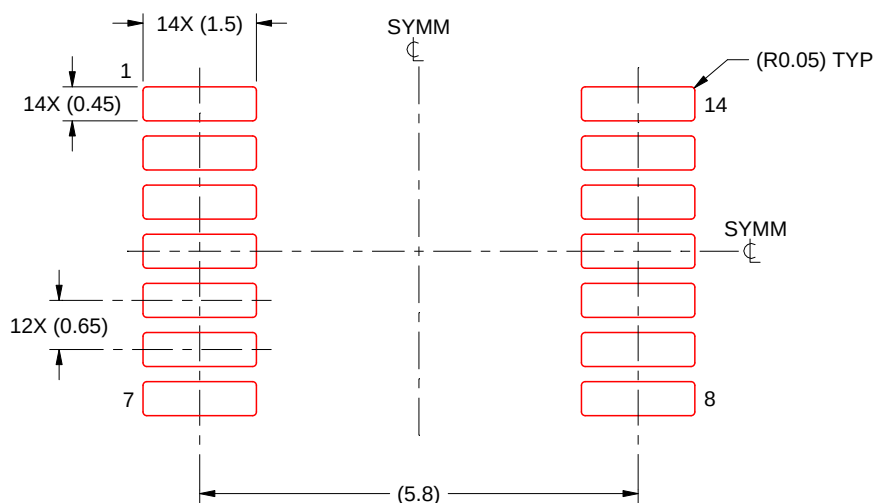
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

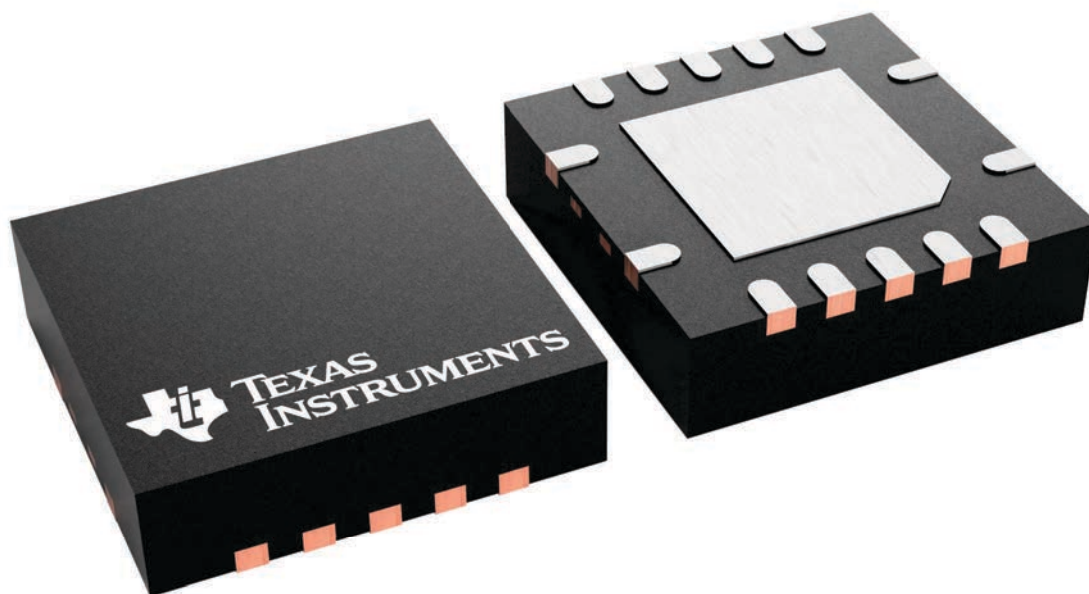
RGY 14

VQFN - 1 mm max height

3.5 x 3.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4231541/A

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